ON Semiconductor

Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

Configurable Multifunction Gate

NL7SZ98

The NL7SZ98 is an advanced high-speed CMOS multifunction gate. The device allows the user to choose logic functions MUX, AND, OR, NAND, NOR, INVERT and BUFFER. The device has Schmitt-trigger inputs, thereby enhancing noise immunity.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 3.3 ns t_{PD} at $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 24 mA at 3.0 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

www.onsemi.com





SC-88/SC70-6/ SOT-363 CASE 419B-02



MARKING



SC-74 CASE 318F-05





UDFN6, 1.45x1.0, 0.5P CASE 517AQ





UDFN6, 1x1, 0.35P CASE 517BX



XXX = Specific Device Code

M = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

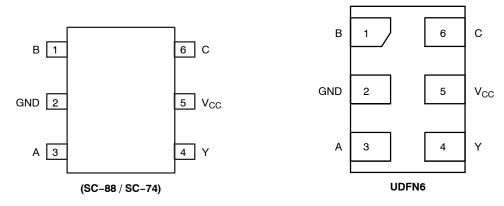


Figure 1. Pinout (Top View)

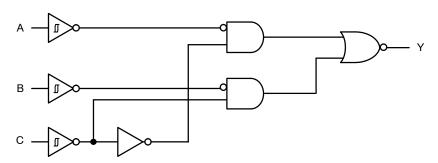


Figure 2. Function Diagram

PIN ASSIGNMENT

Pin	Function
1	В
2	GND
3	А
4	Y
5	V _{CC}
6	С

FUNCTION TABLE*

	Input					
Α	В	С	Υ			
L	L	L	Н			
L	L	Н	Н			
L	Н	L	L			
L	Н	Н	Н			
Н	L	L	Н			
Н	L	Н	L			
Н	Н	L	L			
Н	Н	Н	L			

^{*}To select a logic function, please refer to "Logic Configurations section".

LOGIC CONFIGURATIONS

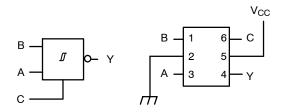


Figure 3. 2-Input MUX with Output Inverted

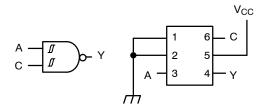


Figure 4. 2-Input NAND (When B = "L")

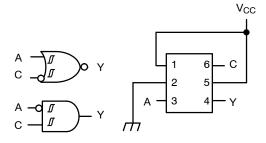


Figure 5. 2-Input NOR with Input C Inverted (When B = "H")

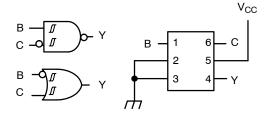


Figure 6. 2-Input NAND with Input C Inverted (When A = "L")

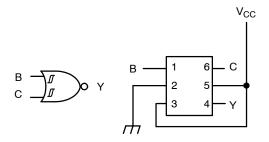


Figure 7. 2-Input NOR (When A ="H")

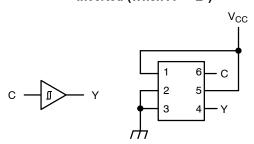


Figure 8. Buffer (When A = "L" and B = "H")

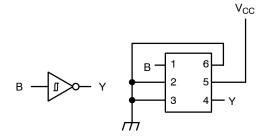


Figure 9. Inverter (When A = C = "L")

MAXIMUM RATINGS

Symbol	Param	neter	Value	Unit
V_{CC}	DC Supply Voltage	SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{IN}	DC Input Voltage	SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	DC Output Voltage SC-88 (NLV)	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage SC-88, SC-74, UDFN6	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
lok	DC Output Diode Current	V _{OUT} < GND	-50	mA
l _{OUT}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Gro	und Pin	±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 1	0 Secs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
P_{D}	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating Oxygen	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Mode Charged Device Model (NLV) Charged Device Model	>2000 >200 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)	(NLV)	±500 ±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri–stated.

- Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
 CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.

 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Pai	Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V_{CC} = 0 V)	0	5.5	V
T _A	Operating Free-Air Temperature		-55	+125	°C
t _r , t _f	Input Rise or Fall Rate	$\begin{aligned} V_{CC} &= 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} &= 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} &= 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} &= 4.5 \text{ V to } 5.5 \text{ V} \end{aligned}$	0 0 0	No Limit No Limit No Limit No Limit	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C			S ≤ T _A B5°C		C ≤ T _A 25°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _T +	V _T + Positive Input		1.65	-	-	1.4	-	1.4	-	1.4	V
	Threshold Voltage		2.3	-	-	1.8	-	1.8	-	1.8	
			3.0	-	-	2.2	-	2.2	-	2.2	
			4.5	-	-	3.1	-	3.1	-	3.1	
			5.5	-	-	3.6	-	3.6	-	3.6	
V _T -	Negative Input		1.65	0.2	-	-	0.2	-	0.2	-	V
	Threshold Voltage		2.3	0.4	-	-	0.4	-	0.4	-	
			3.0	0.6	-	-	0.6	-	0.6	-	
			4.5	1.0	-	-	1.0	-	1.0	-	
			5.5	1.2	-	-	1.2	-	1.2	-	
V_{H}	Input Hysteresis		1.65	0.1	0.48	0.9	0.1	0.9	0.1	-	V
	Voltage		2.3	0.25	0.75	1.1	0.25	1.1	0.25	-	
			3	0.4	0.93	1.2	0.4	1.2	0.4	-	
			4.5	0.6	1.2	1.5	0.6	1.5	0.6	-	
			5.5	0.7	1.4	1.7	0.7	1.7	0.7	-	
V _{OH}	High-Level Output Voltage	I _{OH} = -50 μA	1.65 to 5.5	V _{CC} - 0.1	V _{CC}	-	V _{CC} - 0.1	-	V _{CC} - 0.1	-	V
	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -4 mA	1.65	1.20	1.52	-	1.20	-	1.20	-	
		I _{OH} = -8 mA	2.3	1.9	2.1	-	1.9	-	1.9	-	
		I _{OH} = -16 mA	3	2.4	2.7	-	2.4	-	2.4	-	
		I _{OH} = -24 mA	3	2.3	2.5	-	2.3	-	2.3	-	
		I _{OH} = -32 mA	4.5	3.8	4	-	3.8	-	3.8	-	
V _{OL}	Low-Level Output Voltage	I _{OL} = 100 μA	1.65 to 5.5	-	-	0.1	-	0.1	-	0.1	V
	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 4 mA	1.65	-	0.08	0.45	-	0.45	-	0.45	
		I _{OL} = 8 mA	2.3	-	0.2	0.3	-	0.3	-	0.4	
		I _{OL} = 16 mA	3	-	0.28	0.4	-	0.4	-	0.5	
		I _{OL} = 24 mA	3	-	0.38	0.55	-	0.55	-	0.55	
		I _{OL} = 32 mA	4.5	-	0.42	0.55	-	0.55	-	0.65	1
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-	-	+0.1	-	+1.0	-	+1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	-	10	-	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5	-	-	1.0	-	10	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

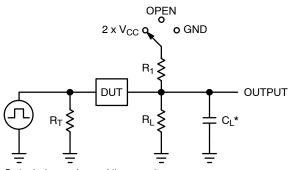
AC ELECTRICAL CHARACTERISTICS

				7	Γ _A = 25°(C		S ≤ T _A B5°C		≤ T _A 25°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , Propagation Delay, (A or B or C) to Y (Figures 10 and 11)	$R_L = 1 \text{ k}\Omega,$ $C_L = 30 \text{ pF}$	1.65 to 1.95	-	8.6	14.4	-	14.4	-	14.4	ns	
	$R_L = 500 \Omega$, $CL = 30 pF$	2.3 to 2.7	-	5.1	8.3	-	8.3	-	8.3		
		R _L = 500 Ω,	3.0 to 3.6	-	3.9	6.3	_	6.3	-	6.3	
		C _L = 50 pF	4.5 to 5.5	_	3.3	5.1	_	5.1	_	5.1	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.0 V, V_{IN} = 0 V or V_{CC}	16 19.5	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$ is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position	C _L , pF	R_L, Ω	R ₁ , Ω		
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table				
t _{PLZ} / t _{PZL}	2 x V _{CC}	50	500	500		
t _{PHZ} / t _{PZH}	GND	50	500	500		

X = Don't Care

C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 Ω) f=1 MHz

Figure 10. Test Circuit

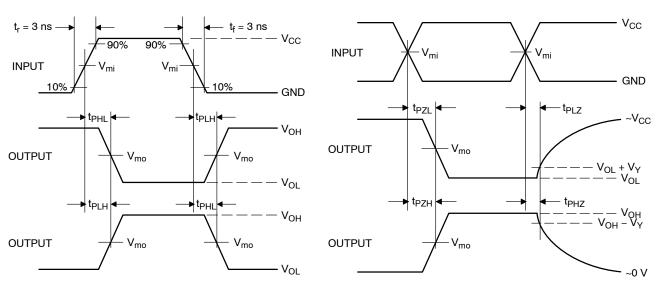


Figure 11. Switching Waveforms

		,		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	0.15
2.3 to 2.7	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	0.15
3.0 to 3.6	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	0.3
4.5 to 5.5	V _{CC} / 2	V _{CC} / 2	V _{CC} / 2	0.3

ORDERING INFORMATION

Device	Package			Shipping [†]
NL7SZ98DFT2G	SC-88 (Pb-Free)	MP	Q4	3000 / Tape & Reel
NLV7SZ98DFT2G*	SC-88 (Pb-Free)	MP	Q4	3000 / Tape & Reel
NL7SZ98DBVT1G (In Development)	SC-74 (Pb-Free)	AP	Q4	3000 / Tape & Reel
NL7SZ98MU1TCG (In Development)	UDFN6, 1.45 x 1.0, 0.5P (Pb-Free)	TBD	Q4	3000 / Tape & Reel
NL7SZ98MU3TCG (In Development)	UDFN6, 1.0 x 1.0, 0.35P (Pb-Free)	TBD	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Pin 1 Orientation in Tape and Reel

Direction of Feed

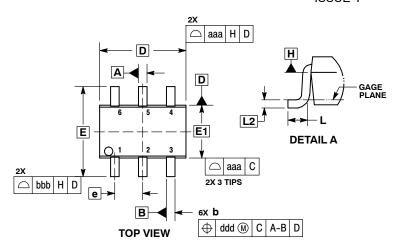


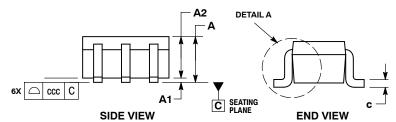
Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE Y**





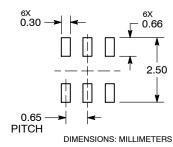
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION

- DIMENSION 5 DOES NOT INCLUDE DAMBAR PROTRUSION.
 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN
 EXCESS OF DIMENSION 5 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER

	MIL	LIMETE	RS		INCHES	3
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BS	С	0	.026 BS	С
L	0.26	0.36	0.46	0.010	0.014	0.018
L2		0.15 BSC			0.006 BS	SC
aaa		0.15			0.006	
bbb	0.30				0.012	
ССС	0.10				0.004	
ddd		0.10			0.004	

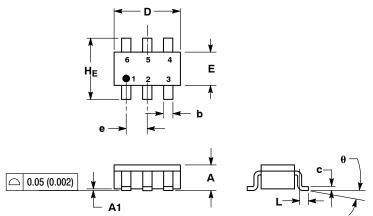
RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

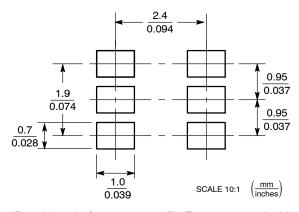
SC-74 CASE 318F-05 **ISSUE N**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
 THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
 THICKNESS OF BASE MATERIAL.
 4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			S INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	_	10°	0°	_	10°

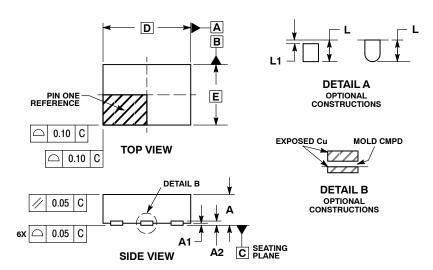
SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

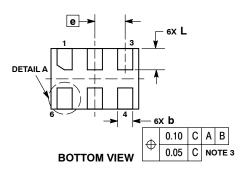
PACKAGE DIMENSIONS

UDFN6, 1.45x1.0, 0.5P CASE 517AQ ISSUE O

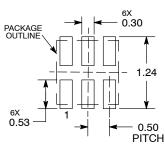


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A2	0.07 REF	
b	0.20	0.30
D	1.45 BSC	
Е	1.00 BSC	
е	0.50 BSC	
L	0.30	0.40
L1		0.15



MOUNTING FOOTPRINT

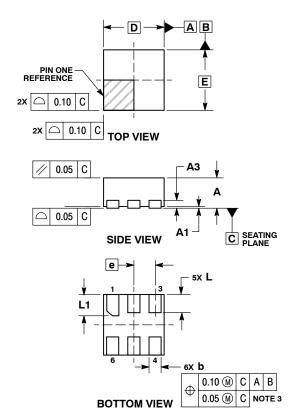


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN6, 1x1, 0.35P CASE 517BX **ISSUE O**

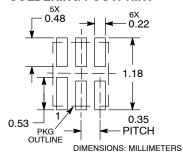


NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION 6 APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS	
DIM	MIN	MAX
Α	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.12	0.22
D	1.00 BSC	
E	1.00 BSC	
е	0.35 BSC	
L	0.25	0.35
L1	0.30	0.40

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. Coverage may be accessed at www.onsemi.com/site/par/-atent_-warking.pgr. On Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Logic Gates category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

74HC85N NLU1G32AMUTCG NLV7SZ58DFT2G CD4068BE NL17SG32P5T5G NL17SG86DFT2G NLV14001UBDR2G
NLX1G11AMUTCG NLX1G97MUTCG 74LS38 74LVC32ADTR2G MC74HCT20ADTR2G NLV17SZ00DFT2G NLV17SZ02DFT2G
NLV74HC02ADR2G 74HC32S14-13 74LS133 74LVC1G32Z-7 M38510/30402BDA 74LVC1G86Z-7 74LVC2G08RA3-7
NLV74HC08ADTR2G NLV74HC14ADR2G NLV74HC20ADR2G NLX2G86MUTCG 5962-8973601DA 74LVC2G02HD4-7
NLU1G00AMUTCG 74LVC2G32RA3-7 74LVC2G00HD4-7 NL17SG02P5T5G 74LVC2G00HK3-7 74LVC2G86HK3-7
NLX1G99DMUTWG NLVVHC1G00DFT2G NLVHC1G08DFT2G NLV7SZ57DFT2G NLV74VHC04DTR2G NLV27WZ86USG
NLV27WZ00USG NLU1G86CMUTCG NLU1G08CMUTCG NL17SZ32P5T5G NL17SZ00P5T5G NL17SH02P5T5G 74AUP2G00RA3-7
NLV74HC02ADTR2G NLX1G332CMUTCG NL17SG86P5T5G NL17SZ05P5T5G